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Stocking Distributor

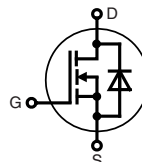
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[IXYS Corporation](#)
[IXKR47N60C5](#)

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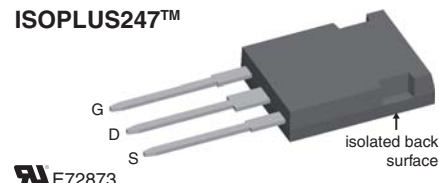
CoolMOS™ 1) Power MOSFET

Electrically isolated back surface
 2500 V electrical isolation
 N-Channel Enhancement Mode
 Low $R_{DS(on)}$, high V_{DSS} MOSFET
 Ultra low gate charge



$V_{DSS} = 600\text{ V}$
 $I_{D25} = 47\text{ A}$
 $R_{DS(on) \text{ max}} = 45\text{ m}\Omega$

ISOPLUS247™



MOSFET			
Symbol	Conditions	Maximum Ratings	
V_{DSS}	$T_{VJ} = 25^\circ\text{C}$	600	V
V_{GS}		± 20	V
I_{D25}	$T_C = 25^\circ\text{C}$	47	A
I_{D90}	$T_C = 90^\circ\text{C}$	32	A
E_{AS}	single pulse } $I_D = 11\text{ A}; T_C = 25^\circ\text{C}$ repetitive	1950	mJ
E_{AR}		3	mJ
dV/dt	MOSFET dV/dt ruggedness $V_{DS} = 0 \dots 480\text{ V}$	50	V/ns

Features

- Silicon chip on Direct-Copper-Bond substrate
 - high power dissipation
 - isolated mounting surface
 - 2500 V electrical isolation
 - low drain to tab capacitance (< 30 pF)
- Fast CoolMOS™ 1) power MOSFET 4th generation
 - high blocking capability
 - lowest resistance
 - avalanche rated for unclamped inductive switching (UIS)
 - low thermal resistance due to reduced chip thickness
- Enhanced total power density

Symbol	wiConditions	Characteristic Values			
		(T _{VJ} = 25°C, unless otherwise specified)			
		min.	typ.	max.	
$R_{DS(on)}$	$V_{GS} = 10\text{ V}; I_D = 44\text{ A}$		40	45	mΩ
$V_{GS(th)}$	$V_{DS} = V_{GS}; I_D = 3\text{ mA}$	2.5	3	3.5	V
I_{DSS}	$V_{DS} = V_{DSS}; V_{GS} = 0\text{ V}$			10	μA
	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 150^\circ\text{C}$		50		μA
I_{GSS}	$V_{GS} = \pm 20\text{ V}; V_{DS} = 0\text{ V}$			100	nA
C_{iss}	$V_{GS} = 0\text{ V}; V_{DS} = 100\text{ V}$ $f = 1\text{ MHz}$		6800		pF
C_{oss}				320	
Q_g	$V_{GS} = 0\text{ to }10\text{ V}; V_{DS} = 400\text{ V}; I_D = 44\text{ A}$		150	190	nC
Q_{gs}			35		nC
Q_{gd}			50		nC
$t_{d(on)}$	$V_{GS} = 10\text{ V}; V_{DS} = 400\text{ V}$ $I_D = 44\text{ A}; R_G = 3.3\ \Omega$		30		ns
t_r			20		ns
$t_{d(off)}$			100		ns
t_f			10		ns
R_{thJC}	with heatsink compound			0.45	K/W
R_{thCH}			0.25		K/W

Applications

- Switched mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)
- Power factor correction (PFC)
- Welding
- Inductive heating
- PDP and LCD adapter

Advantages

- Easy assembly: no screws or isolation foils required
- Space savings
- High power density
- High reliability

¹⁾ CoolMOS™ is a trademark of Infineon Technologies AG.

Source-Drain Diode

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
(T _{VJ} = 25°C, unless otherwise specified)				
I _S	V _{GS} = 0 V		44	A
V _{SD}	I _F = 44 A; V _{GS} = 0 V	0.9	1.2	V
t _{rr}	I _F = 44 A; -di _F /dt = 100 A/μs; V _R = 400 V	600		ns
Q _{RM}		17		μC
I _{RM}		60		A

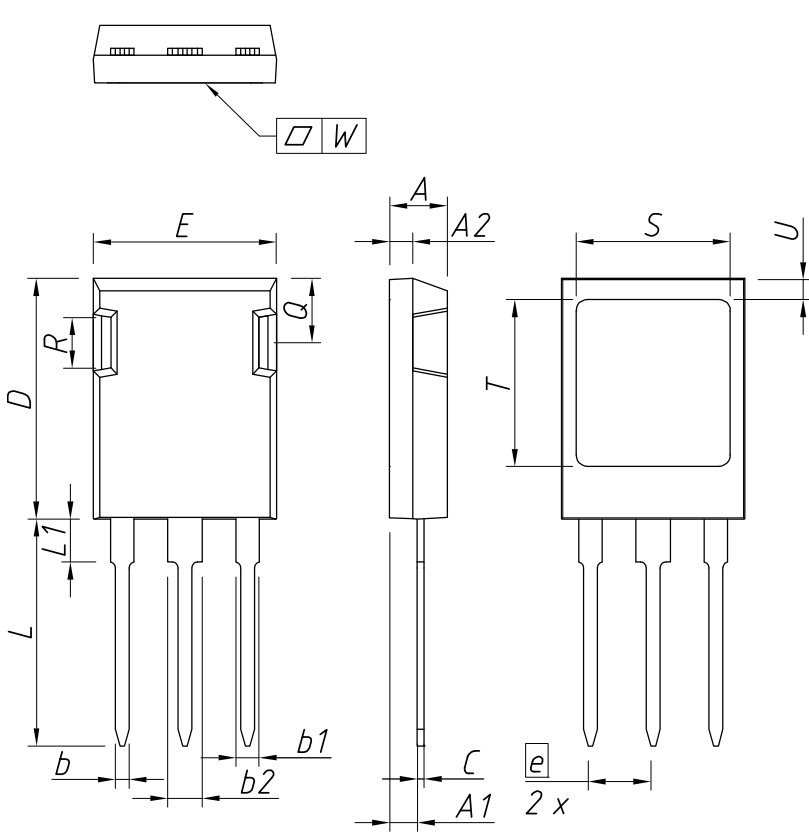
Component

Symbol	Conditions	Maximum Ratings	
T _{VJ}	operating	-55...+150	°C
T _{stg}	storage	-55...+150	°C
V _{ISOL}	I _{ISOL} = 1 mA, 50/60 Hz, t = 1 min	2500	V~
F _C	mounting force with clip	20-120	N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
C _P	coupling capacity between shorted pins and mounting tab in the case		30	pF
d _S , d _A	pin - pin	tbd		mm
d _S , d _A	pin - backside metal	tbd		mm
Weight			6	g

IXYS Advanced Technical Information **IXKR 47N60C5**

ISOPLUS247™ Outline



DIM.	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	4,83	5,21	0,190	0,205
A1	2,29	2,54	0,090	0,100
A2	1,91	2,16	0,075	0,085
b	1,14	1,40	0,045	0,055
b1	1,91	2,15	0,075	0,085
b2	2,92	3,20	0,115	0,126
C	0,61	0,83	0,024	0,033
D	20,80	21,34	0,819	0,840
E	15,75	16,13	0,620	0,635
e	5,45 BSC		0,215 BSC	
L	19,81	20,60	0,780	0,811
L1	3,81	4,38	0,150	0,172
Q	5,59	6,20	0,220	0,244
R	4,32	4,85	0,170	0,191
S	13,21	13,72	0,520	0,540
T	15,75	16,26	0,620	0,640
U	1,65	2,03	0,065	0,080
W	-	0,10	-	0,004

Die konvexe Form des Substrates ist typ. < 0.04 mm über der Kunststoffoberfläche der Bauteilunterseite
 The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side

Die Gehäuseabmessungen entsprechen dem Typ TO-247 AD gemäß JEDEC außer Schraubloch und L_{max}.
 This drawing will meet all dimensions requirement of JEDEC outline TO-247 AD except screw hole and except L_{max}.

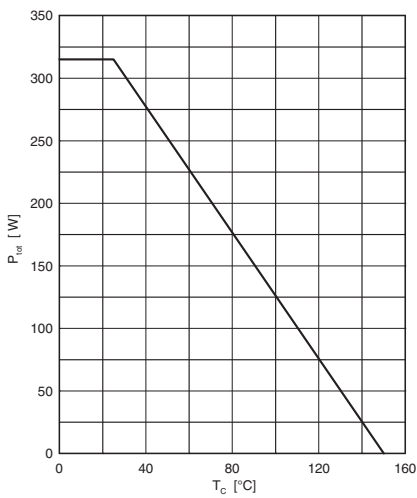


Fig. 1 Typ. power dissipation

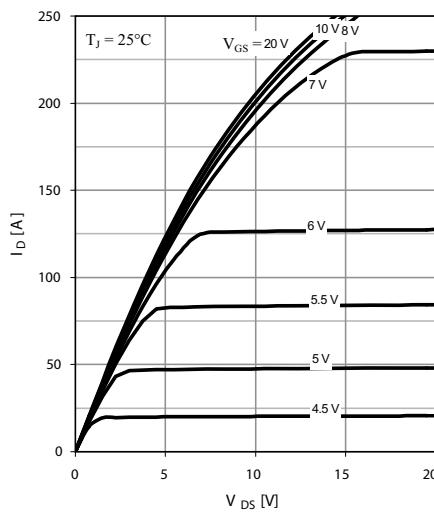


Fig. 2 Typ. output characteristics

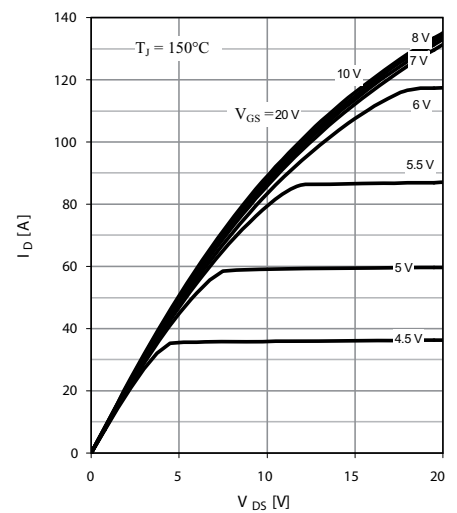


Fig. 3 Typ. output characteristics

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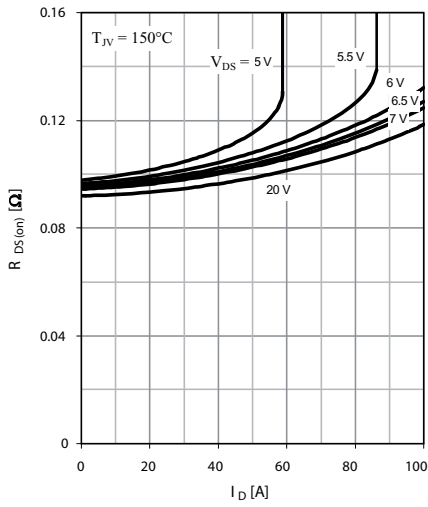


Fig. 4 Typ. drain-source on-state resistance

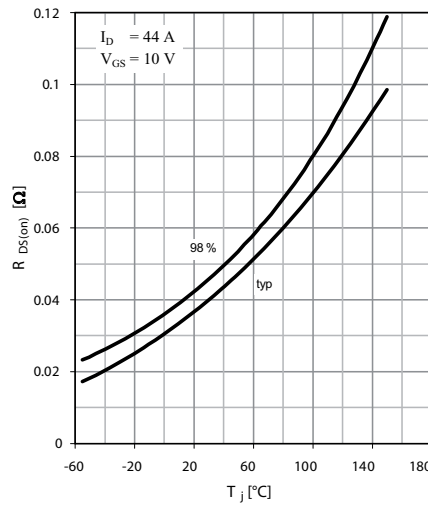


Fig. 5 Drain-source on-state resistance

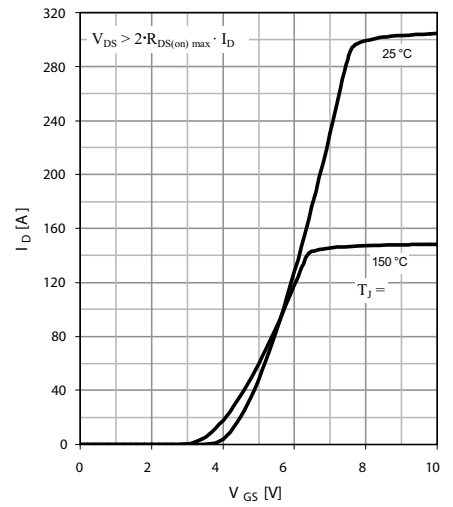


Fig. 6 Typ. transfer characteristics

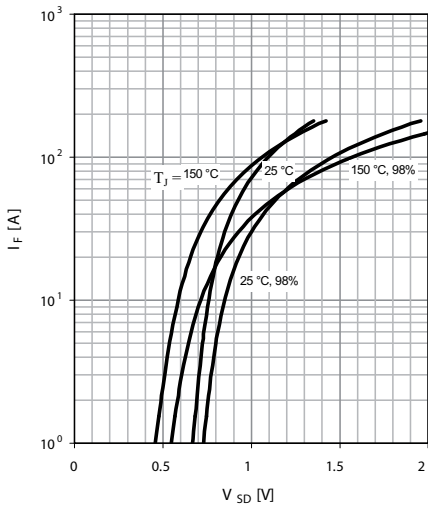


Fig. 7 Forward characteristic of reverse diode

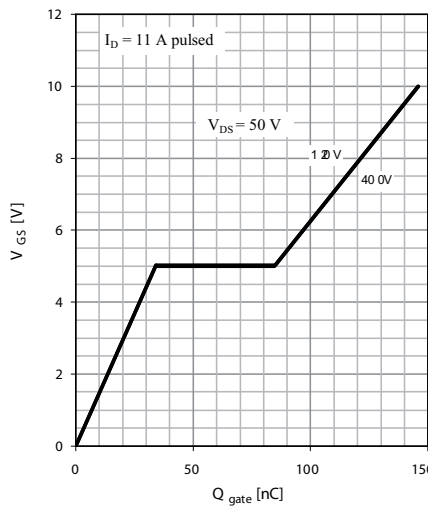


Fig. 8 Typ. gate charge

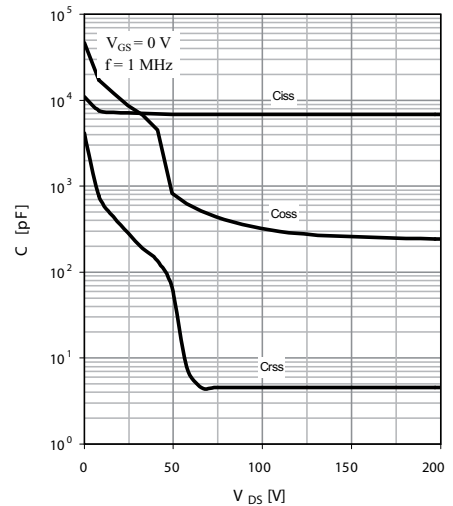


Fig. 9 Typ. capacitances

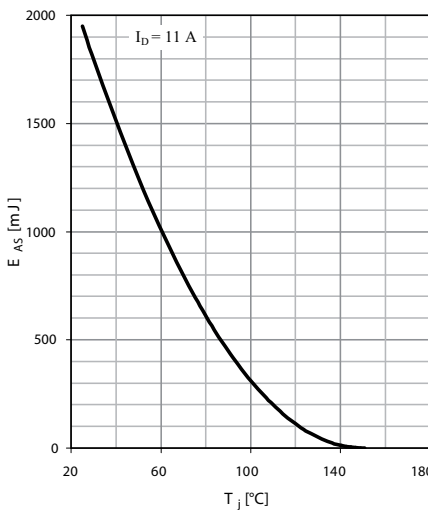


Fig. 9 Avalanche energy

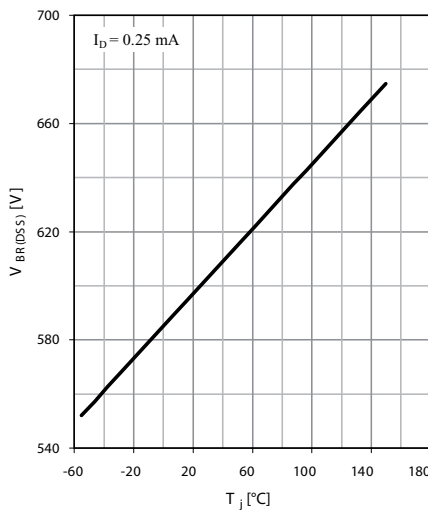


Fig. 10 Drain-source breakdown voltage

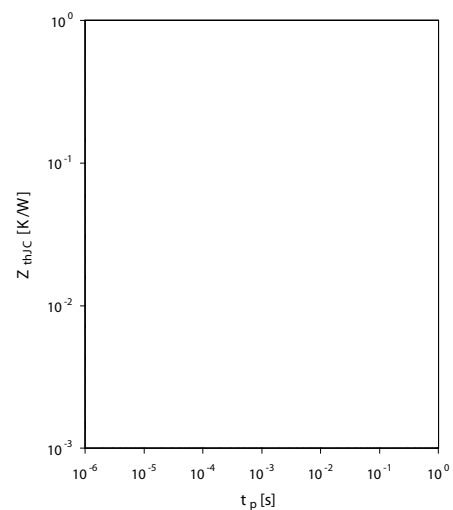


Fig. 12 Max. transient thermal impedance